

# **Silicon Power Transistor**

# 2SA1988

# PNP SILICON TRANSISTOR POWER AMPLIFIER INDUSTRIAL USE

### DESCRIPTION

The 2SA1988 is PNP Silicon Power Transistor that designed for audio frequency power amplifier.

#### FEATURES

- High Voltage VCEO = -200 V
- DC Current Gain hFE = 70 to 200
- TO-3P Package

#### ORDERING INFORMATION

| Type Number | Package |
|-------------|---------|
| 2SA1988     | MP-88   |

#### ABSOLUTE MAXIMUM RATINGS (TA = 25 °C)

| Collector to Base Voltage                     | Vсво          | -200        |
|---|---------------|-------------|
| Collector to Emitter Voltage                  | Vceo          | -200        |
| Emitter to Base Voltage                       | Vebo          | -5.0        |
| Collector Current (DC)                        | IC (DC)       | -7.0        |
| Collector Current (pulse)                     | IC (pulse) *1 | -10         |
| Total Power Dissipantion                      | P2 *2         | 100         |
| JunctionTemperature                           | TJ            | 150         |
| Storage Tempreature                           | Tstg          | –55 to +150 |
| *1 PW $\leq$ 300 $\mu$ s, Duty Cycle $\leq$ 1 | 10 % *2       | Tc = 25 °C  |

#### PACKAGE DIMENSIONS



## ELECTRICAL CHARACTERISTICS (TA = 25 °C)

| CHARACTERISTIC               | SYMBOL    | MIN. | TYP. | MAX. | UNIT | TEST CONDITIONS                                    |
|------------------------------|-----------|------|------|------|------|--|
| Collector Cutoff Current     | Ісво      |      |      | -50  | μA   | $V_{CB} = -200 \text{ V}, \text{ I}_{E} = 0$       |
| Emitter Cutoff Current       | Іево      |      |      | -50  | μA   | $V_{EB} = -3.0 V$ , Ic = 0                         |
| DC Current Gain              | hfe1      | 70   |      | 200  | _    | Vce = -5.0 V, Ic = -1.0 A *                        |
| DC Current Gain              | hFE2      | 20   |      |      | _    | Vce = -5.0 V, Ic = -3.5 A *                        |
| Collector Saturation Voltage | VCE (sat) |      | -0.6 | -2.0 | V    | Ic = -5.0 V, IE = -0.5 V *                         |
| Base Saturation Voltage      | VBE (sat) |      | -1.3 | -2.0 | V    | $I_{C} = -5.0 \text{ V}, I_{E} = -0.5 \text{ V}$ * |
| Gain Band width Product      | f⊤        |      | 40   |      | MHz  | Vce = -5.0 V, Ic = 1.0 mA                          |
| Output Capacitance           | Cob       |      | 270  |      | pF   | $V_{CB} = -10 V$ , $I_C = 0$ , $f = 1.0 MHz$       |

V

V

V

A A W °C °C

\* Pulse Test PW  $\leq$  350  $\mu$ s, Duty Cycle  $\leq$  2 %

The information in this document is subject to change without notice.



#### TRANSIENT THERMAL RESISTANCE vs. PULSE WIDTH







OUTOPUT CAPASITANCE VS COLLECTOR TO BASE VOLTAGE I⊧=0 f=1MHz Cob - Output Cpacitance - pF 1 000 100 10 -1000 -0.1 -1.0 -10 -100 VCB - Collector to Base Voltage -V

#### REFERENCE

| Document Name   | Document No. |
|---|--------------|
| NEC semiconductor device reliability/quality control system | TEI-1202     |
| Quality grade on NEC semiconductor devices                  | IEI-1209     |
| Semiconductor device mounting technology manual             | C10535E      |
| Semoconductor device package manual                         | C10943X      |
| Guide to quality assurance for semiconductor devices        | MEI-1202     |
| Semiconductor selection guide                               | X10679E      |

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- Special: Transportation equipment (automobiles, trains, ships, etc.), traffic control systems, anti-disaster systems, anti-crime systems, safety equipment and medical equipment (not specifically designed for life support)
- Specific: Aircrafts, aerospace equipment, submersible repeaters, nuclear reactor control systems, life support systems or medical equipment for life support, etc.

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Anti-radioactive design is not implemented in this product.